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Abstract

PURPOSE: To realize a semiconductor device controlled at an atomic level by manufacturing a crystalline substrate having a sufficiently wide terrace part required for device operation.

CONSTITUTION: A crystalline substrate 1((a)) after surface polishing in which a terrace part 11 and a step part 12 are ununiformly distributed is subjected to growth by atomic layer epitaxy and is irradiated with light having spatial periodicity. The pattern of the terrace part 11 and the step part 12 is uniformized, and the step part 12 is multiplexed to spread the terrace part 11 ((b)).